





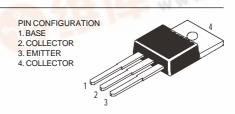
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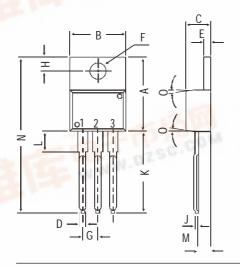
# TO-220 Plastic Package

CSB507, CSD313

# CSB507 PNP PLASTIC POWER TRANSISTOR CSD313 NPN PLASTIC POWER TRANSISTOR

Low frequency Power Amplifier Applications





	DIM	MIN.	MAX.	
diminsions in mm.	Α	14.42	16.51	
	В	9.63	10.67	
	С	3.56	4.83	
	D		0.90	
	Ε	1.15	1.40	
	F	3.75	3.88	
	G	2.29	2.79	
	Н	2.54	3.43	
	J		0.56	
	K	12.70	14.73	
	L	2.80	4.07	
	М	2.03	2.92	
	N		31.24	
Ē	0	DEG 7		

### ABSOLUTE MAXIMUM RATINGS

Collector-base voltage (open emitter)	$V_{CBO}$	max.	60 V
Collector-emitter voltage (open base)	$V_{CEO}$	max.	60 V
Collector current	$I_C$	max.	3.0 A
Total power dissipation up to $T_C = 25^{\circ}C$	$P_{tot}$	max.	30 W
Junction temperature	$T_{j}$	max.	150 ℃
Collector-emitter saturation voltage	J		
$I_C = 2A$ ; $I_B = 0.2A$	$V_{CEsat}$	max.	1.0 V
D.C. current gain			
$I_C = 1A$ ; $V_{CE} = 2V$	$h_{\!F\!E}$	min	40
		max.	320

# **RATINGS** (at $T_A$ =25°C unless otherwise specified)

Limiting values
Collector-base voltage (open emitter)
Collector-emitter voltage (open base)
Emitter-base voltage (open collector)

 VCBO
 max.
 60 V

 VCEO
 max.
 60 V

 VEBO
 max.
 5.0 V



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## CSB507, CSD313

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Collector current	$I_C$	max.	3.0 A
Collector current (Peak value)	$I_{CM}$	max.	8.0 A
Total power dissipation up to $T_C = 25^{\circ}C$	$P_{tot}$	max.	30 W
Junction temperature	$T_j$	max.	150 ℃
Storage temperature	$T_{Stg}$	-65 to	+150 ℃
THERMAL CHARACTERISTICS			
From junction to case	$R_{thj-c}$	=	4.17 CW
CHARACTERISTICS			
$T_{amb} = 25$ °C unless otherwise specified			
Collector cutoff current			
$I_E = 0$ ; $V_{CB} = 20V$	$I_{CBO}$	max.	0.1 mA
$I_B = 0$ ; $V_{CE} = 60V$	$I_{CEO}$	max.	5.0  mA
Emitter cut-off current			
$I_C = 0$ ; $V_{EB} = 4V$	$I_{EBO}$	max.	1.0 mA
Breakdown voltages			
$I_C = 1 \text{ mA}; I_B = 0$	$V_{C\!E\!O}$	min.	60 V
$I_C = 1 \text{ mA}; I_E = 0$	$V_{CBO}$	min.	60 V
$I_E = 1 \text{ mA; } I_C = 0$	$V_{EBO}$	min.	5.0 V
Saturation voltage			
$I_C = 2 A$ ; $I_B = 0.2 A$	$V_{CEsat}^*$	max.	1.0 V
Base emitter on voltage	02541		
$I_C = 1A$ ; $V_{CF} = 2V$	$V_{BE(on)}^*$	max.	1.5 V
D.C. current gain	DL(OII)		
$I_C = 0.1A$ ; $V_{CE} = 2V$	$h_{\!F\!E}^*$	min.	40
$I_C = 1A; V_{CE} = 2V^{**}$	$h_{\!F\!E}^*$	min.	40
C , CL	TL.	max.	320
Transition frequency			
$I_C = 500 \text{ mA}; V_{CE} = 5V$	$f_T$	typ.	8 MHz
10 - 300 HE1, V CE - 3V	11	typ.	O WILL

<sup>\*</sup> Pulse test: pulse width  $\leq$  300  $\mu$ s; duty cycle  $\leq$  2.0%.

<sup>\*\*</sup> h<sub>FE</sub> classification: C: 40-80 D: 60-120 E: 100-200 F: 160-320

### **Disclaimer**

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